



## 30 A, 1200 V, Hyperfast Diode

The RHRP30120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

### Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRP30120	TO-220AC	RHR30120

NOTE: When ordering, use the entire part number.

### Symbol



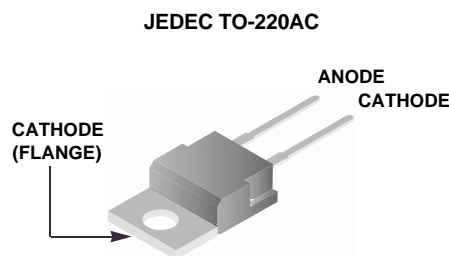
### Features

- Hyperfast Recovery  $t_{rr} = 85$  ns (@  $I_F = 30$  A)
- Max Forward Voltage,  $V_F = 3.2$  V (@  $T_C = 25^\circ\text{C}$ )
- 1200 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

### Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

### Packaging



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

	RHRP30120	UNIT
Peak Repetitive Reverse Voltage . . . . .	$V_{RRM}$ 1200	V
Working Peak Reverse Voltage . . . . .	$V_{RWM}$ 1200	V
DC Blocking Voltage . . . . .	$V_R$ 1200	V
Average Rectified Forward Current . . . . . ( $T_C = 78^\circ\text{C}$ )	$I_{F(AV)}$ 30	A
Repetitive Peak Surge Current . . . . . (Square Wave, 20 kHz)	$I_{FRM}$ 60	A
Nonrepetitive Peak Surge Current . . . . . (Halfwave, 1 Phase, 60 Hz)	$I_{FSM}$ 300	A
Maximum Power Dissipation . . . . .	$P_D$ 125	W
Avalanche Energy (See Figures 7 and 8) . . . . .	$E_{AVL}$ 30	mJ
Operating and Storage Temperature . . . . .	$T_{STG}, T_J$ -65 to 175	$^\circ\text{C}$

**Electrical Specifications**  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
$V_F$	$I_F = 30\text{ A}$	-	-	3.2	V
	$I_F = 30\text{ A}, T_C = 150^\circ\text{C}$	-	-	2.6	V
$I_R$	$V_R = 1200\text{ V}$	-	-	250	$\mu\text{A}$
	$V_R = 1200\text{ V}, T_C = 150^\circ\text{C}$	-	-	1	mA
$t_{rr}$	$I_F = 1\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	-	65	ns
	$I_F = 30\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	-	85	ns
$t_a$	$I_F = 30\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	48	-	ns
$t_b$	$I_F = 30\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	22	-	ns
$R_{\theta JC}$		-	-	1.2	$^\circ\text{C}/\text{W}$

**DEFINITIONS**

$V_F$  = Instantaneous forward voltage ( $p_w = 300\mu\text{s}$ ,  $D = 2\%$ ).

$I_R$  = Instantaneous reverse current.

$T_{rr}$  = Reverse recovery time (See Figure 6), summation of  $t_a + t_b$ .

$t_a$  = Time to reach peak reverse current (See Figure 6).

$t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 6).

$R_{\theta JC}$  = Thermal resistance junction to case.

$p_w$  = pulse width.

$D$  = duty cycle.

**Typical Performance Curves**

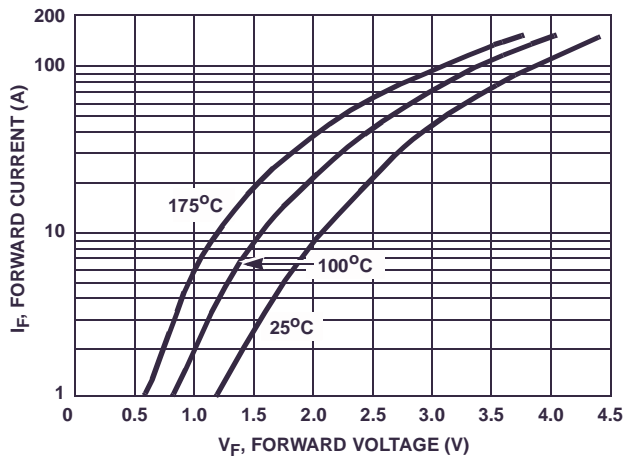


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

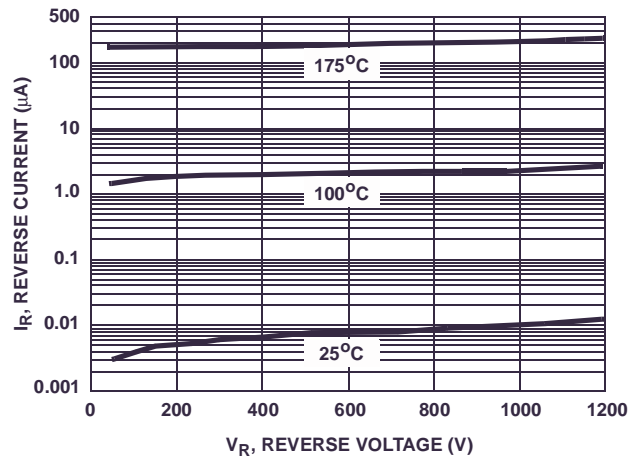


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

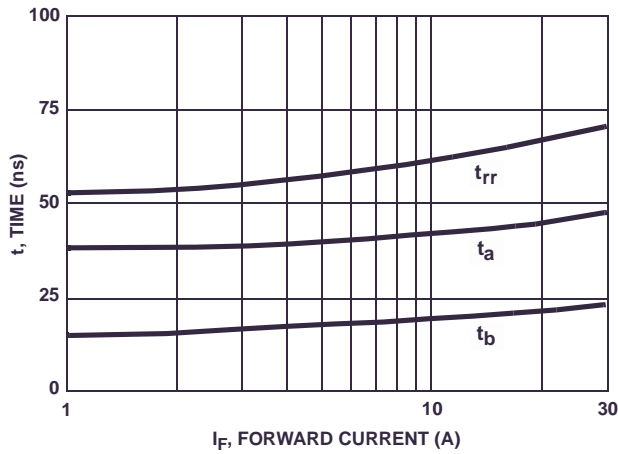


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

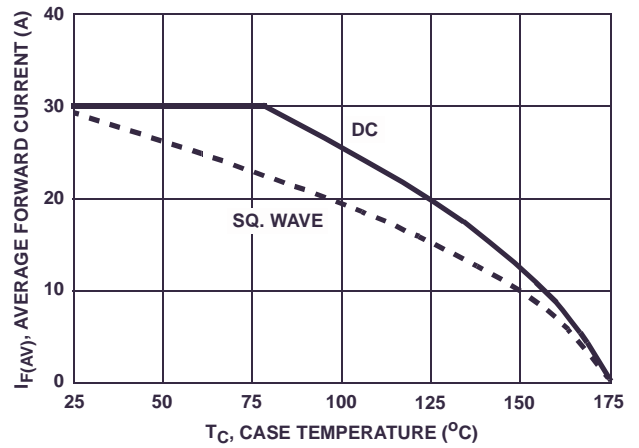


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

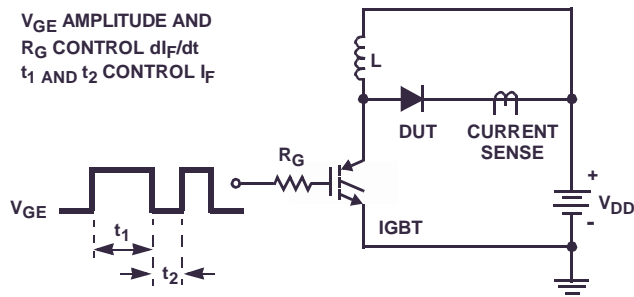


FIGURE 5.  $t_{rr}$  TEST CIRCUIT

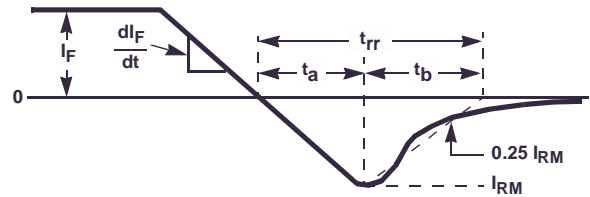


FIGURE 6.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1.225A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

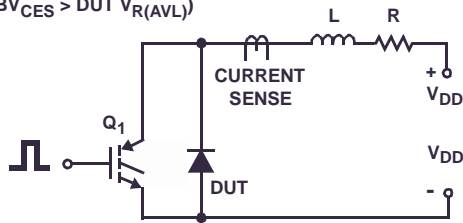


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

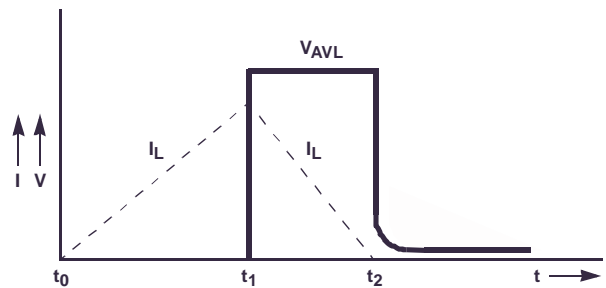


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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